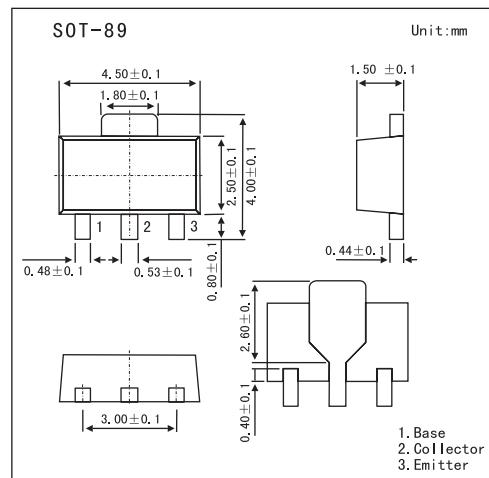


Silicon PNP Epitaxial Planar Type

2SB1599

■ Features

- Low collector to emitter saturation voltage VCE(sat).
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-40	V
Emitter-base voltage	V _{EBO}	-5	V
Peak collector current	I _{CP}	-3	A
Collector current	I _C	-0.6	A
Collector power dissipation	P _C	1	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = -20 V, I _E = 0			-1	μA
	I _{CEO}	V _{CE} = -12 V, I _B = 0			-100	μA
Emitter cutoff current	I _{EBO}	V _{EB} = -5 V, I _C = 0			-100	μA
Collector-base voltage	V _{CBO}	I _C = -1 mA, I _E = 0	-50			V
Collector-emitter voltage	V _{CEO}	I _C = -10 mA, I _B = 0	-40			V
Forward current transfer ratio	h _{FE}	V _{CE} = -5 V, I _C = -1A	50		220	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -1.5A, I _B = - 0.15A		-0.4	-1	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -2A, I _B = - 0.2A			-1.5	V
Transition frequency	f _T	V _{CB} = -5 V, I _E = 0.5 A, f = 200 MHz		150		MHz
Collector output capacitance	C _{ob}	V _{CB} = -5V, I _E = 0, f = 1 MHz		70		pF

■ h_{FE} Classification

Marking	1X		
Rank	P	Q	R
h _{FE}	50~100	80~160	100~220